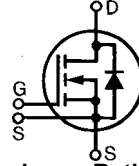


HiPerFET™ Power MOSFETs

IXFN 200 N06
IXFN 200 N07

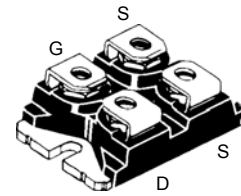
N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}



V_{DSS}	I_{D25}	$R_{DS(on)}$
60 V	200 A	6 mΩ
70 V	200 A	6 mΩ

$t_{rr} \leq 250$ ns

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate D = Drain
S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	N07	70 V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	N06	60 V
V_{GS}	Continuous		± 20 V
V_{GSM}	Transient		± 30 V
I_{D25}	$T_C = 25^\circ\text{C}$; Chip capability	200N06	200 A
$I_{L(RMS)}$	Terminal current limit		100 A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}		600 A
I_{AR}	$T_C = 25^\circ\text{C}$		100 A
E_{AR}	$T_C = 25^\circ\text{C}$		30 mJ
E_{AS}	$T_C = 25^\circ\text{C}$		2 J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A/ns}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_{\theta JC} = 2\ \Omega$		5 V/ns
P_D	$T_C = 25^\circ\text{C}$		520 W
T_J			-55 ... +150 °C
T_{JM}			150 °C
T_{stg}			-55 ... +150 °C
V_{ISOL}	10/50 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s		- 2500 V~ - 3000 V~
M_d	Mounting torque Terminal connection torque		1.5/13 Nm/lb.in. - 1.5/13 Nm/lb.in.
Weight			30 g

NOT FOR NEW DESIGN

Features

- International standard packages
- miniBLOC with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

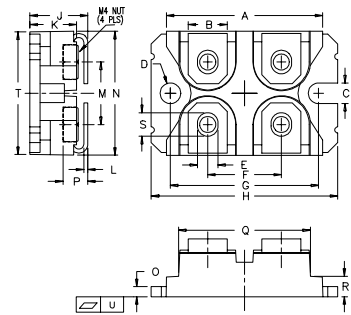
- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
			min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	N06 N07	60 70		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{ mA}$		2		4 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$				± 200 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 125^\circ\text{C}$ $V_{GS} = 0\text{ V}$		2		400 μA mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$				6 mΩ

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	60	80	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9000	pF
C_{oss}			4000	pF
C_{rss}			2400	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		30	ns
t_r			60	ns
$t_{d(off)}$			100	ns
t_f			60	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		480	nC
Q_{gs}			60	nC
Q_{gd}			240	nC
R_{thJC}	miniBLOC, SOT-227 B		0.24	K/W
R_{thCK}	miniBLOC, SOT-227 B	0.05		K/W

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_s	$V_{GS} = 0\text{ V}$		200	A
I_{SM}	Repetitive; pulse width limited by T_{JM}		600	A
V_{SD}	$I_F = 100\text{ A}, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$		1.7	V
t_{rr}	$I_F = 25\text{ A}$ $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 50\text{ V}$		150	250 ns
Q_{RM}			0.7	μC
I_{RM}			9	A

IXYS reserves the right to change limits, test conditions, and dimensions.

 IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	